



**TRANSISTORS, HIGH POWER, PNP,  
BASED ON TYPE 2N5153  
ESCC Detail Specification No. 5204/002**

**ISSUE 1  
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	ESCC Detail Specification		PAGE ii ISSUE 1
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Pages 1 to 19

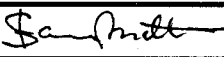
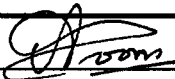
**TRANSISTORS, HIGH POWER, PNP,**

**BASED ON TYPE 2N5153**

**ESA/SCC Detail Specification No. 5204/002**



**space components  
coordination group**

Issue/Rev.	Date	Approved by	
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Issue 4	January 1998		



**DOCUMENTATION CHANGE NOTICE**

Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
		This Issue supersedes Issue 3 and incorporates all modifications defined in Revisions 'A', 'B', 'C' and 'D' to Issue 3 and the changes agreed in the following DCRs:-		
		Cover Page		None
		DCN		None
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		Para. 2	: Item (c) deleted	221401
		Table 1(a)	: Format amended and Variants 04 and 05 added	221401
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			: Nos. 4, "(Continuous)" added to Characteristics	221401
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		Para. 4.7.6	: New Para. 4.7.6 added	221401
		Table 5	: First Table renumbered to "5(b)" and title amended	221401
			: Subtitle added to existing Table and in No. 2, "1" added to Characteristics	221401
			: Table added for Variants 04 to 05	221401
		Figure 5	: First Figure renumbered to "5(b)" and title amended	221401
			: Second Figure numbered as "5(a)" and title amended	221401
		Para. 4.8.1	: Text added at the beginning of the second sentence	221401
		Para. 4.8.2	: Second sentence added	221401
		Para. 4.8.3	: In the second sentence, text amended	221401
		Para. 4.8.4	: Text amended	221401



**TABLE OF CONTENTS**

	<u>Page</u>
<b>1. <u>GENERAL</u></b>	<b>5</b>
1.1 Scope	5
1.2 Component Type Variants	5
1.3 Maximum Ratings	5
1.4 Parameter Derating Information	5
1.5 Physical Dimensions	5
1.6 Functional Diagram	5
1.7 High Temperature Test Precautions	5
<b>2. <u>APPLICABLE DOCUMENTS</u></b>	<b>5</b>
<b>3. <u>TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS</u></b>	<b>5</b>
<b>4. <u>REQUIREMENTS</u></b>	<b>10</b>
4.1 General	10
4.2 Deviations from Generic Specification	10
4.2.1 Deviations from Special In-process Controls	10
4.2.2 Deviations from Final Production Tests	10
4.2.3 Deviations from Burn-in and Electrical Measurements	10
4.2.4 Deviations from Qualification Tests	10
4.2.5 Deviations from Lot Acceptance Tests	10
4.3 Mechanical Requirements	10
4.3.1 Dimension Check	10
4.3.2 Weight	10
4.3.3 Terminal Strength	10
4.4 Materials and Finishes	11
4.4.1 Case	11
4.4.2 Lead Material and Finish	11
4.5 Marking	11
4.5.1 General	11
4.5.2 Lead Identification	11
4.5.3 The SCC Component Number	11
4.5.4 Traceability Information	12
4.6 Electrical Measurements	12
4.6.1 Electrical Measurements at Room Temperature	12
4.6.2 Electrical Measurements at High and Low Temperatures	12
4.6.3 Circuits for Electrical Measurements	12
4.7 Burn-in Tests	12
4.7.1 Parameter Drift Values	12
4.7.2 Conditions for High Temperature Reverse Bias Burn-in	12
4.7.3 Conditions for Power Burn-in	12
4.7.4 Electrical Circuits for High Temperature Reverse Bias Burn-in	12
4.7.5 Electrical Circuits for Power Burn-in	12
4.7.6 Verification of Safe Operating Area	12
4.8 Environmental and Endurance Tests	18
4.8.1 Electrical Measurements on Completion of Environmental Tests	18
4.8.2 Electrical Measurements at Intermediate Points and on Completion of Endurance Tests	18
4.8.3 Conditions for Operating Life Tests	18
4.8.4 Electrical Circuit for Operating Life Tests	18
4.8.5 Conditions for High Temperature Storage Test	18



Page

**TABLES**

1(a)	Type Variants	6
1(b)	Maximum Ratings	6
2	Electrical Measurements at Room Temperature - d.c. Parameters	13
	Electrical Measurements at Room Temperature - a.c. Parameters	14
3	Electrical Measurements at High and Low Temperatures	14
4	Parameter Drift Values	16
5(a)	Conditions for High Temperature Reverse Bias Burn-in	16
5(b)	Conditions for Power Burn-in and Operating Life Tests	17
6	Electrical Measurements at Intermediate Points and on Completion of Endurance Testing	19

**FIGURES**

1	Parameter Derating Information	7
2	Physical Dimensions	8
3	Functional Diagram	9
4	Circuits for Electrical Measurements	15
5(a)	Electrical Circuit for High Temperature Reverse Bias Burn-in	17
5(b)	Electrical Circuit for Power Burn-in and Operating Life Tests	17

**APPENDICES (Applicable to specific Manufacturers only)**

None.

**1. GENERAL****1.1 SCOPE**

This specification details the ratings, physical and electrical characteristics, test and inspection data for a Transistor, High Power, PNP, based on Type 2N5153.

It shall be read in conjunction with ESA/SCC Generic Specification No. 5000, the requirements of which are supplemented herein.

**1.2 COMPONENT TYPE VARIANTS**

Variants of the basic transistors specified herein, which also covered by this specification, are given in Table 1(a).

**1.3 MAXIMUM RATINGS**

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the transistors specified herein, are scheduled in Table 1(b).

**1.4 PARAMETER DERATING INFORMATION**

The derating information applicable to the transistors specified herein is shown in Figure 1.

**1.5 PHYSICAL DIMENSIONS**

The physical dimensions of the transistors specified herein are shown in Figure 2.

**1.6 FUNCTIONAL DIAGRAM**

The functional diagram, showing lead identification, of the transistors specified herein, is shown in Figure 3.

**1.7 HIGH TEMPERATURE TEST PRECAUTIONS**

For tin-lead plated or solder-dipped lead finish, all tests to be performed at a temperature that exceeds + 125°C shall be carried out in 100% inert atmosphere.

**2. APPLICABLE DOCUMENTS**

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors.
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.

**3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS**

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply.

**TABLE 1(a) - TYPE VARIANTS**

VARIANT	BASED ON TYPE	CASE	FIGURE	LEAD MATERIAL AND FINISH
01	2N5153	TO39	2(a)	D2
02	2N5153	TO39	2(a)	D3 or D4
03	2N5153	TO39	2(a)	D7
04	2N5153	TO257	2(b)	H2
05	2N5153	TO257	2(b)	H4

**TABLE 1(b) - MAXIMUM RATINGS**

No.	CHARACTERISTIC	SYMBOL	MAXIMUM RATING	UNIT	REMARKS
1	Collector-Base Voltage	$V_{CBO}$	-100	V	
2	Collector-Emitter Voltage	$V_{CEO}$	-80	V	
3	Emitter-Base Voltage	$V_{EBO}$	-5.5	V	
4	Collector Current (Continuous)	$I_C$	-5.0	A	
5	Power Dissipation 1 Variants 01 to 03 Variants 04 to 05	$P_{tot1}$	1.0 3.3	W	$T_{amb} = +25^{\circ}C$ See Note 1
6	Power Dissipation 2 Variants 01 to 03 Variants 04 to 05	$P_{tot2}$	10 35	W	$T_{case} = +25^{\circ}C$ See Note 1
7	Operating Temperature Range	$T_{op}$	-65 to +200	$^{\circ}C$	$T_{amb}$ or $T_{case}$
8	Storage Temperature Range	$T_{stg}$	-65 to +200	$^{\circ}C$	
9	Soldering Temperature	$T_{sol}$	+260	$^{\circ}C$	Note 2
10	Thermal Resistance Variants 01 to 03 Variants 04 to 05	$R_{TH(J-C)}$	17.5 5.0	$^{\circ}C/W$	

**NOTES**

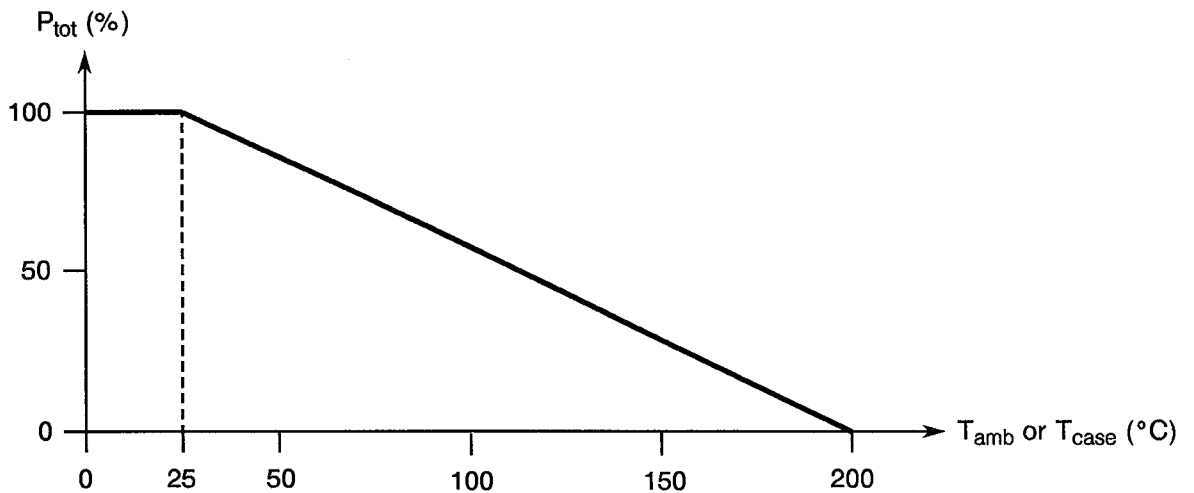
1. For derating at  $T_{amb}$  or  $T_{case} > +25^{\circ}C$ , see Figure 1.
2. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.



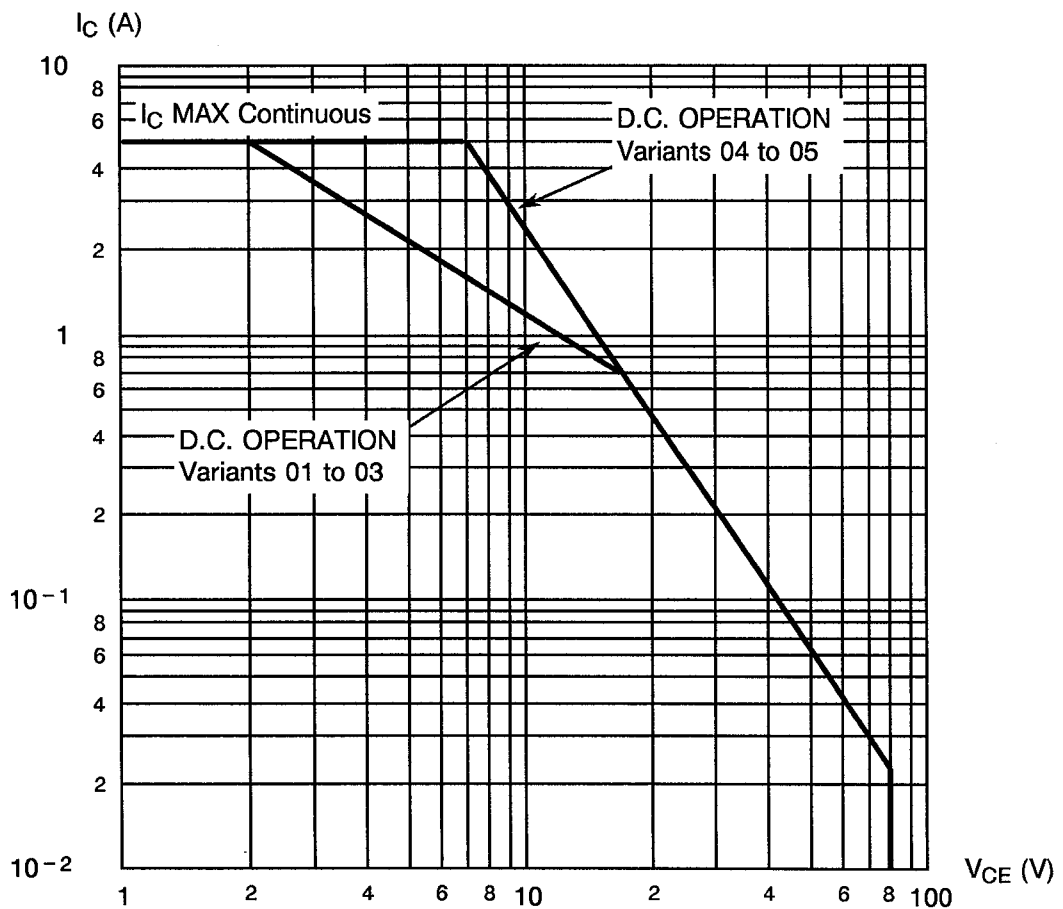


**FIGURE 1 - PARAMETER DERATING INFORMATION**

**FIGURE 1(a) - POWER DISSIPATION VERSUS TEMPERATURE**



**FIGURE 1(b) - FORWARD BIAS SAFE OPERATING AREA (MAXIMUM CONTINUOUS D.C.)**



**Collector Current versus Collector-Emitter Voltage**

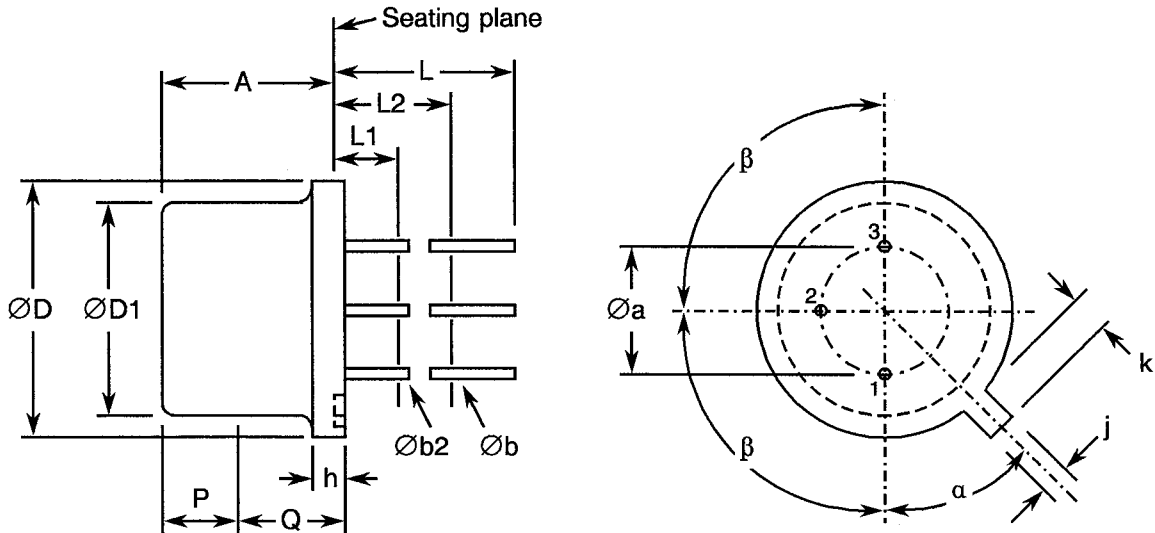
**NOTES**

1. See Para. 4.7.6.



**FIGURE 2 - PHYSICAL DIMENSIONS**

FIGURE 2(a) - VARIANTS 01 TO 03



SYMBOL	MILLIMETRES		NOTES
	MIN.	MAX.	
$\varnothing a$	4.83	5.33	
A	6.10	6.60	
$\varnothing b$	0.406	0.533	2
$\varnothing b2$	0.406	0.483	2
$\varnothing D$	8.89	9.40	
$\varnothing D1$	8.00	8.51	
h	0.229	3.18	
j	0.711	0.864	
k	0.737	1.02	3
l	12.70	-	2
l1	-	1.27	2
l2	6.35	-	2
P	2.54	-	1
Q	-	-	4
$\alpha$	45° NOMINAL		
$\beta$	90° NOMINAL		

**NOTES**

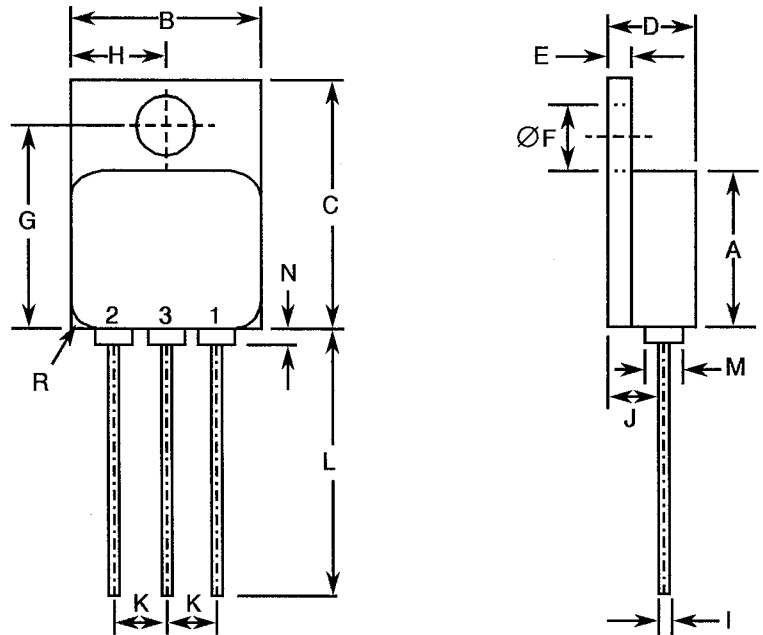
1. This zone is controlled for automatic handling. The variation in actual diameter within this zone shall not exceed 0.254mm.
2. (Three leads)  $\varnothing b2$  applies between  $l1$  and  $l2$ .  $\varnothing b$  applies between  $l2$  and 12.70mm from seating plane. Diameter is uncontrolled in  $l1$  and beyond 12.70mm from seating plane.
3. Measured from maximum diameter of the actual device.
4. Details of outline in this zone optional.



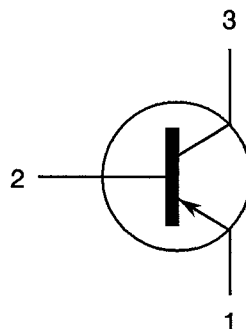
**FIGURE 2 - PHYSICAL DIMENSIONS (CONT.)**

FIGURE 2(b) - VARIANTS 04 to 05

SYMBOL	MILLIMETRES	
	MIN.	MAX.
A	10.41	10.67
B	10.41	10.67
C	16.51	16.76
D	4.7	5.33
E	0.89	1.14
ØF	3.56	3.81
G	13.39	13.64
H	5.13	5.38
I	0.64	0.89
J	2.92	3.18
K	2.41	2.67
L	15.24	16.51
M	2.29 Typical	
N	-	0.71
R	1.65 Typical	



**FIGURE 3 - FUNCTIONAL DIAGRAM**



- 1. Emitter.
- 2. Base.
- 3. Collector.

**NOTES**

- 1. For Variants 01 to 03, the collector is internally connected to the case.
- 2. For Variants 04 to 05, the collector is isolated from the case.

**4. REQUIREMENTS****4.1 GENERAL**

The complete requirements for procurement of the transistors specified herein are stated in this specification and ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors. Deviations from the Generic Specification applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

**4.2 DEVIATIONS FROM GENERIC SPECIFICATION****4.2.1 Deviations from Special In-process Controls**

None.

**4.2.2 Deviations from Final Production Tests (Chart II)**

None.

**4.2.3 Deviations from Burn-in and Electrical Measurements (Chart III)**

None.

**4.2.4 Deviations from Qualification Tests (Chart IV)**

None.

**4.2.5 Deviations from Lot Acceptance Tests (Chart V)**

None.

**4.3 MECHANICAL REQUIREMENTS****4.3.1 Dimension Check**

The dimensions of the transistors specified herein shall be checked. They shall conform to those shown in Figure 2.

**4.3.2 Weight**

The maximum weight of the transistors specified herein shall be 1.5 grammes for Variants 01 to 03 and 5.0 grammes for Variants 04 to 05.

**4.3.3 Terminal Strength**

The requirements for terminal strength testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The test conditions shall be as follows:-

**Variants 01 to 03**

Test Condition : 'E', Lead Fatigue.

**Variants 04 to 05**

Test Condition : 'A' (Tension).

Applied Force : 10 N.

Duration : 10 seconds.



4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the transistors specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 Case

For Variants 01 to 03, the case shall be hermetically sealed and have a metal body with hard glass seals and the lid shall be welded, brazed, preform soldered or glass frit sealed.

For Variants 04 to 05, the case shall be hermetically sealed and have a metal body, the Fe/Ni copper core pin shall pass through a ceramic eyelet brazed into the frame and the lid shall be welded.

4.4.2 Lead Material and Finish

For Variants 01 to 03, the lead material shall be Type 'D' with either Type '2', Type '3 or 4' or Type '7' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

For Variants 04 to 05, the lead material shall be Type 'H' with either Type '2' or Type '4' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700 and the following paragraphs. When the component is too small to accommodate all of the marking specified, as much as space permits shall be marked and the marking information, in full, shall accompany the component in its primary package.

The information to be marked and the order of precedence, shall be as follows:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Lead Identification

Lead identification shall be as shown in Figures 2 and 3.

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

Detail Specification Number \_\_\_\_\_ 520400202B  
Type Variant (see Table 1(a)) \_\_\_\_\_  
Testing Level (B or C, as applicable) \_\_\_\_\_



#### 4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

### 4.6 ELECTRICAL MEASUREMENTS

#### 4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured at room temperature are scheduled in Table 2. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C.

#### 4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3.

#### 4.6.3 Circuits for Electrical Measurements

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 are shown in Figure 4.

### 4.7 BURN-IN TESTS

#### 4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C. The parameter drift values ( $\Delta$ ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

#### 4.7.2 Conditions for High Temperature Reverse Bias Burn-in

The requirements for high temperature reverse bias burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5000. The conditions for high temperature reverse bias burn-in shall be as specified in Table 5(a) of this specification.

#### 4.7.3 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5000. The conditions for power burn-in shall be as specified in Table 5(b) of this specification.

#### 4.7.4 Electrical Circuits for High Temperature Reverse Bias.

Circuits for use in performing the high temperature reverse bias burn-in tests are shown in Figure 5(a) of this specification.

#### 4.7.5 Electrical Circuits for Power Burn-in

Circuits for use in performing the power burn-in tests are shown in Figure 5(b) of this specification.

#### 4.7.6 Verification of Safe Operating Area

The requirement for the verification of the Safe Operating Area are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The test method shall be as follows:-

Maximum continuous d.c. in accordance with MIL-STD-750, Method 3052 and Figure 1(b) of this specification, at  $T_{case} = +25$ °C and for an operating time of 50ms maximum.

For Variants 01 to 05:  $I_C = 0.5A$ ,  $V_{CE} = 18V$ .

**TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS**

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN	MAX	
1	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	3011	$I_C = -100mA$ $I_B = 0A$ Note 1	-80	-	V
2	Collector-Emitter Cut-off Current	$I_{CES}$	3041	$V_{CE} = -60V$ $V_{BE} = 0V$	-	-1.0	$\mu A$
3	Collector-Emitter Cut-off Current	$I_{CEO}$	3041	$V_{CE} = -40V$ $I_B = 0A$	-	-50	$\mu A$
4	Emitter-Base Cut-off Current 1	$I_{EBO1}$	3061	$V_{EB} = -4.0V$ $I_C = 0A$	-	-1.0	$\mu A$
5	Emitter-Base Cut-off Current 2	$I_{EBO2}$	3061	$V_{EB} = -5.5V$ $I_C = 0A$	-	-1.0	mA
6	D.C. Forward Current Transfer Ratio 1	$h_{FE1}$	3076	$V_{CE} = -5.0V$ $I_C = -50mA$ Note 1	50	-	-
7	D.C. Forward Current Transfer Ratio 2	$h_{FE2}$	3076	$V_{CE} = -5.0V$ $I_C = -2.5A$ Note 1	70	200	-
8	D.C. Forward Current Transfer Ratio 3	$h_{FE3}$	3076	$V_{CE} = -5.0V$ $I_C = -5.0A$ Note 1	40	-	-
9	Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	3071	$I_C = -5.0A$ $I_B = -0.5A$ Notes 1 and 2	-	-1.5	V
10	Base-Emitter Saturation Voltage 1	$V_{BE(SAT)1}$	3066	$I_C = -2.5A$ $I_B = -0.25A$ Notes 1 and 2	-	-1.45	V
11	Base-Emitter Saturation Voltage 2	$V_{BE(SAT)2}$	3066	$I_C = -5.0A$ $I_B = -0.5A$ Notes 1 and 2	-	-2.2	V

**NOTES**

1. Pulsed measurement: Pulse Length  $\leq 300\mu s$ , Duty Cycle  $\leq 2.0\%$ .
2. Saturation voltages measured 6.0mm from header.



**TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS**

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST FIG.	TEST CONDITIONS (Note 1)	LIMITS		UNIT
						MIN.	MAX.	
12	A.C. Forward Current Transfer Ratio	$h_{fe}$	3206	-	$V_{CE} = -5.0V$ $I_C = -0.5A$ $f = 20MHz$	3.5	-	-
13	Output Capacitance	$C_{obo}$	3236	-	$V_{CB} = -10V$ $I_E = 0A$ $f = 1.0MHz$	-	250	pF
14	Turn-on Time	$t_{on}$	-	4	$I_C = -5.0A$ $I_{B1} = -0.5A$ $I_{B2} = 0.5A$ $V_{CC} = -30V$ $V_{BB} = 4.0V$ $V_{IN} \approx -51V$	-	0.5	$\mu s$
15	Turn-off Time	$t_{off}$	-	4	$I_C = -5.0A$ $I_{B1} = -0.5A$ $I_{B2} = 0.5A$ $V_{CC} = -30V$ $V_{BB} = 4.0V$ $V_{IN} \approx -51V$	-	1.3	$\mu s$

**NOTES**

1. Measurements performed on a sample basis, LTPD 7 or less.

**TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES**

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN.	MAX.	
2	Collector-Emitter Cut-off Current	$I_{CES}$	3041	$V_{CE} = -60V$ $V_{BE} = 0V$ $T_{amb} = +150^{\circ}C$	-	-10	$\mu A$
7	D.C. Forward Current Transfer Ratio 2	$h_{FE2}$	3076	$V_{CE} = -5.0V$ $I_C = -2.5A$ $T_{amb} = -55^{\circ}C$ Note 1	35	-	-

**NOTES**

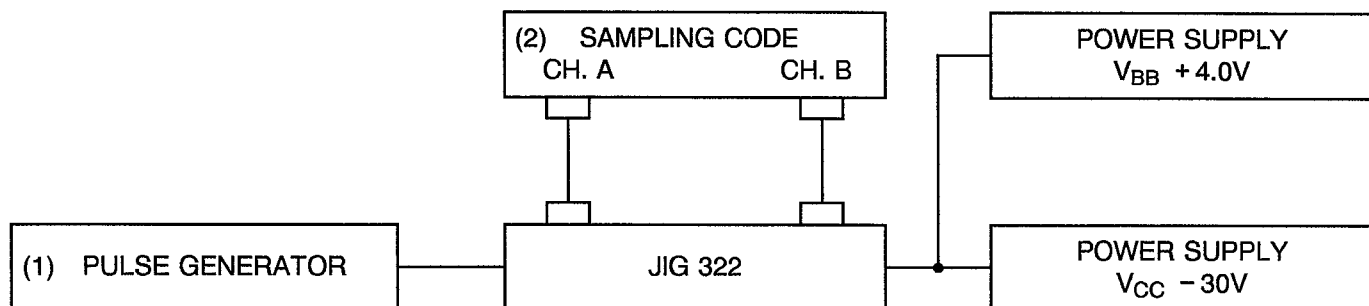
1. Pulsed measurement: Pulse Length  $\leq 300\mu s$ , Duty Cycle  $\leq 2.0\%$ .



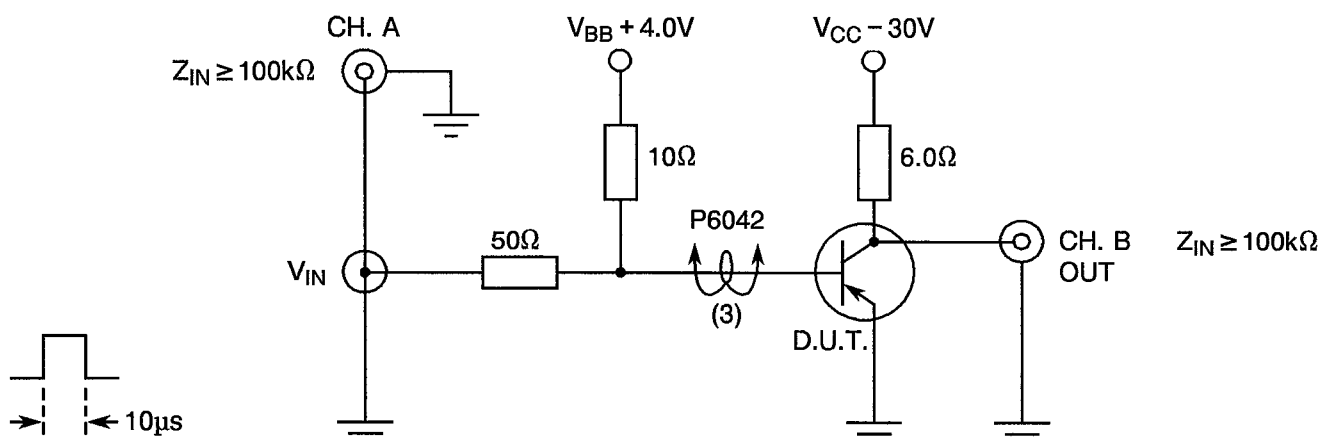


**FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS**

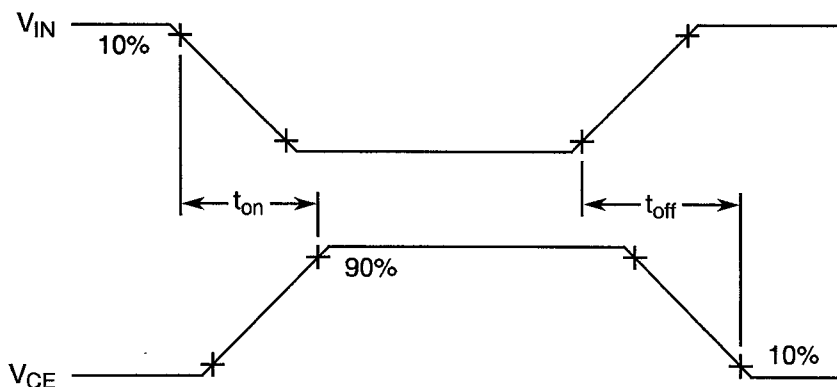
BLOCK DIAGRAM



EQUIVALENT TEST CIRCUIT



VOLTAGE WAVEFORMS



**NOTES**

1. Pulse generator Type EH132 or equivalent,  $t_r \leq 20\text{ns}$ ,  $t_p = 10\mu\text{s}$ , Duty Cycle = 1.0%.
2. Sampling Scope Tetronics 568 or equivalent.
3. Adjust  $V_{IN} - V_B$  with current probe P6042.

**TABLE 4 - PARAMETER DRIFT VALUES**

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITION	CHANGE LIMITS ( $\Delta$ )	UNIT
2	Collector-Emitter Cut-off Current	$I_{CES}$	As per Table 2	As per Table 2	$\pm 100$	nA
7	D.C. Forward Current Transfer Ratio 2	$h_{FE2}$	As per Table 2	As per Table 2	$\pm 25$	%
9	Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	As per Table 2	As per Table 2	$\pm 100$	mV

**TABLE 5(a) - CONDITIONS FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN**

No.	CHARACTERISTIC	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	$T_{amb}$	+ 150	$^{\circ}C$
2	Collector-Base Voltage	$V_{CB}$	- 60	V
3	Emitter-Base Voltage	$V_{EB}$	- 4.5	V
4	Duration	t	48	Hours

**TABLE 5(b) - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TESTS****VARIANTS 01 TO 03**

No.	CHARACTERISTIC	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	$T_{amb}$	+ 20 to + 50 (1)	$^{\circ}C$
2	Power Dissipation 1	$P_{tot1}$	Max. rating at $T_{amb}$ according to derating curve (See Figure 1(a))	W
3	Collector-Base Voltage	$V_{CB}$	- 20	V

**NOTES**

1. No heat sink nor forced air directly on the device shall be permitted.

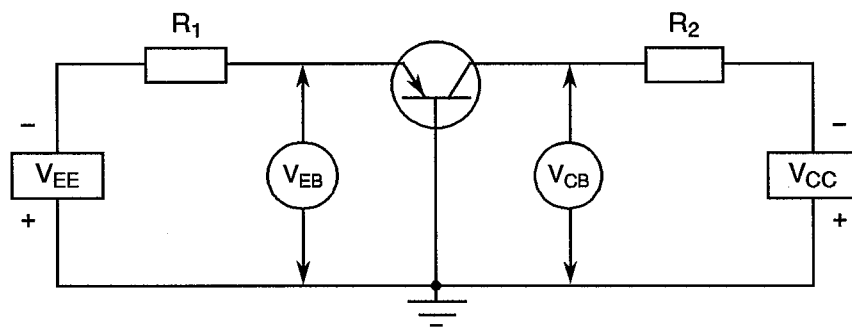


**TABLE 5(b) - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TESTS (CONT.)**

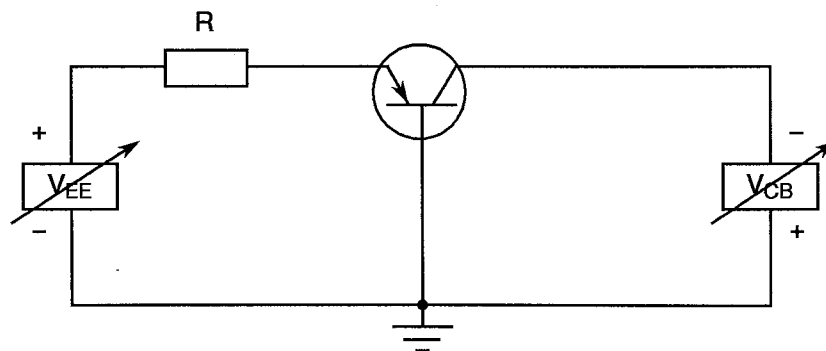
VARIANTS 04 TO 05

No.	CHARACTERISTIC	SYMBOL	CONDITION	UNIT
1	Case Temperature	$T_{case}$	+ 100(+ 0 - 5)	°C
2	Power Dissipation 2	$P_{tot2}$	Max. rating at $T_{case}$ according to derating curve (See Figure 1(a))	W
3	Collector-Base Voltage	$V_{CB}$	- 20	V

**FIGURE 5(a) - ELECTRICAL CIRCUIT FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN**



**FIGURE 5(b) - ELECTRICAL CIRCUIT FOR POWER BURN-IN AND OPERATING LIFE TESTS**





- 4.8 ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC SPECIFICATION NO. 5000)
- 4.8.1 Electrical Measurements on Completion of Environmental Tests  
The parameters to be measured on completion of environmental tests are scheduled in Table 2. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C.
- 4.8.2 Electrical Measurements at Intermediate Points and on Completion of Endurance Tests  
The parameters to be measured at intermediate points and on completion of endurance testing are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C.
- 4.8.3 Conditions for Operating Life Tests (Part of Endurance Testing)  
The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The conditions for operating life testing shall be the same as specified in Table 5(b) for the power burn-in test.
- 4.8.4 Electrical Circuit for Operating Life Tests  
The circuit to be used for performance of the operating life test shall be the same as shown in Figure 5(b) for power burn-in.
- 4.8.5 Conditions for High Temperature Storage Test (Part of Endurance Testing)  
The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 5000. The temperature to be applied shall be the maximum storage temperature specified in Table 1(b) of this specification.

**SCC**ESA/SCC Detail Specification  
No. 5204/002

PAGE 19

ISSUE 4

**TABLE 6 - ELECTRICAL MEASUREMENTS AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING**

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITION	LIMITS		UNIT
					MIN.	MAX.	
2	Collector-Emitter Cut-off Current	$I_{CES}$	As per Table 2	As per Table 2	-	-1.0	$\mu A$
7	D.C. Forward Current Transfer Ratio 2	$h_{FE2}$	As per Table 2	As per Table 2	70	200	-
9	Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	As per Table 2	As per Table 2	-	-1.5	V